

To calculate bith voltage gain a overall voltage gain, we need the parameters for ro & gm, which he find by working out the DC bias pint.

(10,11'd over)

Experiment 1 ENC Analog Denies If we consider large signals only then the impedence gets very large for the capacitor R Xc = /wc Xc -po as w-so. Homes the capacitors act as short cirwits and we ger the Bllowing large Light model. PI MANY to God Va Q_1 Me want to God Va Q_2 Me $V_4 = \begin{bmatrix} R_3 \\ Q_1 + R_2 + R_3 \end{bmatrix}$. V_9 . $V_9 = \begin{bmatrix} 145.5 \\ 500 \end{bmatrix}$. $V_9 = \begin{bmatrix} 2.91 \\ 2.91 \\ 100 \end{bmatrix}$ Now, - Vs + IBRS - DU = O. $V_2 = I_B R_b - 10 - 1$ Further, if the dense is is saturation, we get that: Is = 1/2 kn (Vas - VT)2. : $ID = \frac{1}{2} kn \left(V_q - V_3 - V_7 \right)^2 - 2$ Sub in equal) to equal 2) to get: $I_D = \frac{1}{2} k_n (2.91 - I_D. R_s + 10 - 2)^2$ $ID = \frac{2.4e-3}{2} (2.91 - 10 \text{ K. ID} + 10 - 2)^2$

Experiment 1 ENG Hading Darlow. Large Dignal Analysis. .. ID = (10.91 - 10k.ID)2. 833.33 ID = 119.02 - 218200 ID + 1006 ID 100eb ID - 219033.33ID + 119.02 =0. In = 9,999 e-4A ID = 10e-4A (Note: ID < 0 for the other sols of was)

ID = 1mA. (Note: ID < 0 for the other sols of was) If ID = IMA then Vo = 10 - IMA. 7K Vo = 10 -7 VD = 3 als, Vs = -10 + IMA. 10K. Vz = OV. Vp - Vs > Va - Vs - Vr => Device is actually in Saturation, w Bias Covert ID = ImA. · Hence, 9m = Mulox W Vov = 2.4mA/V2. (2.91-2) gm= 2.4e-3 (0.91) \$

= 2.184e-3 S

(corld over).

Fx periment 1 FNC1 Analog Devices

Finally, ignoring the effect of 10 the

Voltage gain is:

$$Av = -9m (RB11RL)$$
= -2.18te-3 ($\frac{1}{7K} + \frac{1}{10k}$)-1
= -8.9929.

Av = -9 %

Overall voltage gain is:

The max value or the voltage gain in the Pspice Simulation is approx 20 %, which doesn't resoncte to the results derived here.